

L Number	Hits	Search Text	DB	Time stamp
1	569	"buried strap" (bottle adj1 trenches) (bottle adj1 trench)	USPAT; US-PGPUB; EPO; JPO	2004/06/12 09:23
2	63	("buried strap" (bottle adj1 trenches) (bottle adj1 trench) ) adj3 (remov\$3 etch\$3)	USPAT; US-PGPUB; EPO; JPO	2004/06/12 09:23
-	12772	438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.	USPAT; US-PGPUB; EPO; JPO	2004/06/12 09:22
-	4797	(438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:12
-	4483	((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:13
-	4297	((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and etch\$3	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:13
-	2780	(((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and etch\$3) and polysilicon	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:13
-	403	((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and etch\$3) and pmos	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:14

-	1501	(438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and (void voids residue)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:14
-	761	((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and (voids void residue)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:14
-	0	((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and (voids void residue)) and salient	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:14
-	48	((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and (voids void residue)) and (protru\$4) salient and semiconductor	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:22
-	1948	salient and semiconductor	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:23
-	324	(salient and semiconductor) and ("silicon nitride" sin)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:23
-	240	((salient and semiconductor) and ("silicon nitride" sin)) and ("silicon oxide" oxide sio2)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:28
-	438	((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and (voids void residue)) and polysilicon	USPAT; US-PGPUB; EPO; JPO	2004/06/02 15:29

-	274	(((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and (voids void residue)) and polysilicon) and sidewall\$1	USPAT; US-PGPUB; EPO; JPO	2004/06/02 16:17
-	2047	(sidewalls sidewall "insulation collar") near3 ("silicon nitride" SiN)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 16:17
-	591	((sidewalls sidewall "insulation collar") near3 ("silicon nitride" SiN)) same (portion part protruding protrusion residue remainder)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 16:18
-	559	((((sidewalls sidewall "insulation collar") near3 ("silicon nitride" SiN)) same (portion part protruding protrusion residue remainder)) and etch\$3	USPAT; US-PGPUB; EPO; JPO	2004/06/02 16:19
-	545	((((sidewalls sidewall "insulation collar") near3 ("silicon nitride" SiN)) same (portion part protruding protrusion residue remainder)) and etch\$3) not ((((438/199.cccls. 438/200.cccls. 438/230.cccls. 438/239.cccls. 438/243.cccls. 438/270.cccls. 438/444.cccls. 438/445.cccls. 438/446.cccls. 438/696.cccls. 438/697.cccls. 438/700.cccls. 438/704.cccls. 438/706.cccls. 438/745.cccls. 438/748.cccls. 438/754.cccls. 257/301.cccls. 257/532.cccls. 257/204.cccls. 257/277.cccls. 257/516.cccls. 438/245.cccls. 438/386-388.cccls.) and ("silicon nitride" SiN)) and ("silicon oxide" oxide sio2)) and (voids void residue)) and polysilicon) and sidewall\$1)	USPAT; US-PGPUB; EPO; JPO	2004/06/02 16:19
-	569	"buried strap" (bottle adj1 trenches) (bottle adj1 trench)	USPAT; US-PGPUB; EPO; JPO	2004/06/12 09:23
-	1	5244843.pn.	USPAT	2004/06/12 08:51
-	1	5244843.pn. and native	USPAT	2004/06/12 08:51